

## ABSTRACT OF THE DISCLOSURE

A first moisture blocking layer formed of a silicon type nitride film such as SiNx or the like is formed over the entire surface so as to cover a drain electrode and a source electrode of a TFT. On the first moisture blocking layer, a first planarization film formed of an organic material is provided. On the first planarization film, a second moisture blocking layer formed of SiNx or the like is provided. In the peripheral region, the second moisture blocking layer extends down on the first moisture blocking layer and is connected with the first moisture blocking layer. Also, a sealing glass is bonded to the second moisture blocking layer using the sealing member. By enclosing the first planarization film by the first moisture blocking layer and the second moisture blocking layer, intrusion of external moisture can be effectively prevented.